This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

1-2. (Canceled)

3-4. (Withdrawn)

5. (Previously amended): A method of forming semiconductor transistors, comprising:

forming a gate electrode over but insulated from a semiconductor body region for each of first and second transistors;

forming off-set spacers along side-walls of the gate electrode of each of the first and second transistors;

after forming said off-set spacers, performing a DDD implant to form DDD source and DDD drain regions in the body region for the first transistor;

after forming said off-set spacers, performing a LDD implant to form LDD source and LDD drain regions for the second transistor;

after both said DDD and LDD implants, forming main spacers adjacent the off-set spacers of the first and second transistors; and

after forming said main spacers, performing a source/drain (S/D) implant to form a highly doped region within each of the DDD drain and DDD source regions and each of the LDD drain and LDD source regions, the highly doped regions being of the same conductivity type as and having a doping concentration greater than the DDD and LDD regions.

6. (Previously amended): The method of claim 5 wherein,

the extent of an overlap between the gate electrode of the first transistor and each of the DDD source and DDD drain regions, and the extent of an overlap

between the gate electrode of the second transistor and each of the LDD source and LDD drain regions is inversely dependent on a thickness of the off-set spacers,

a distance between an outer edge of each of the DDD source and DDD drain regions and an outer edge of the corresponding highly doped region within each of the DDD source and DDD drain regions is directly dependent on a thickness of the main spacers, and

a distance between an outer edge of each of the LDD source and LDD drain regions and an outer edge of the corresponding highly doped region within each of the LDD source and LDD drain regions is directly dependent on a thickness of the main spacers.

7. (Original): The method of claim 5 wherein N- type impurities is used in each of the DDD and LDD implants, and N+ type impurities is used in the S/D implant.

8. (Original): The method of claim 5 wherein P- type impurities is used in each of the DDD and LDD implants, and P+ type impurities is used in the S/D implant.

9. (Withdrawn)

10. (Canceled)

11-12. (Withdrawn)

13-17. (Canceled)

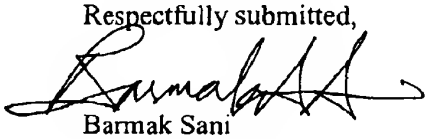
18. (Withdrawn)

19-99. (Canceled)

CONCLUSION

If the Examiner believes a telephone conference would expedite prosecution of this application, please telephone the undersigned at 650.326.2400.

Respectfully submitted,



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